

2SA1194(K)

Silicon PNP Epitaxial

HITACHI

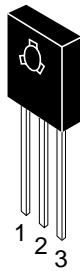
ADE-208-854 (Z)
1st. Edition
Sep. 2000

Application

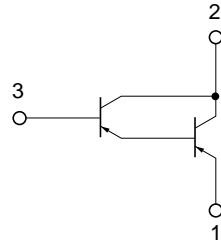
High gain amplifier

Outline

TO-126 MOD



1. Emitter
2. Collector
3. Base



Absolute Maximum Ratings (T_a = 25°C)

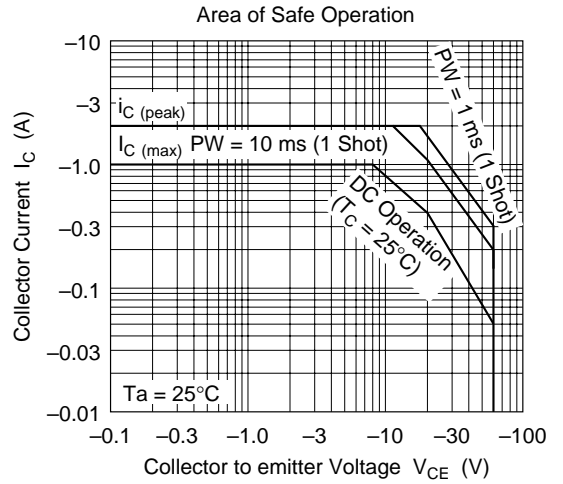
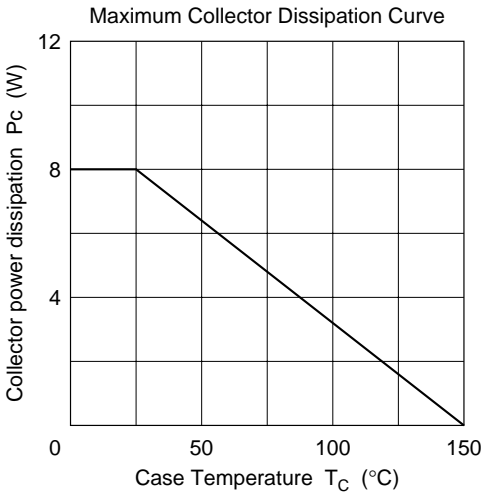
Item	Symbol	Rating	Unit
Collector to base voltage	V _{CBO}	-60	V
Collector to emitter voltage	V _{CEO}	-60	V
Emitter to base voltage	V _{EBO}	-7	V
Collector current	I _C	-1	A
Collector peak current	I _{C(peak)}	-2	A
Collector power dissipation	P _C	1	W
	P _C *1	8	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

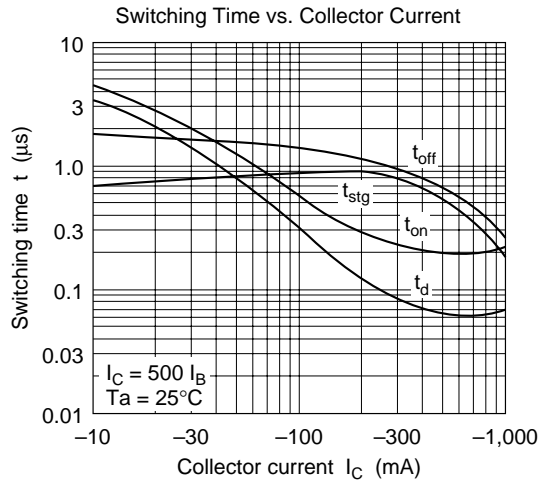
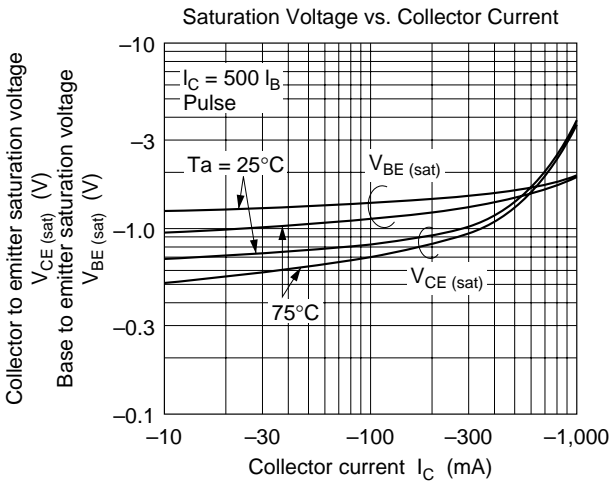
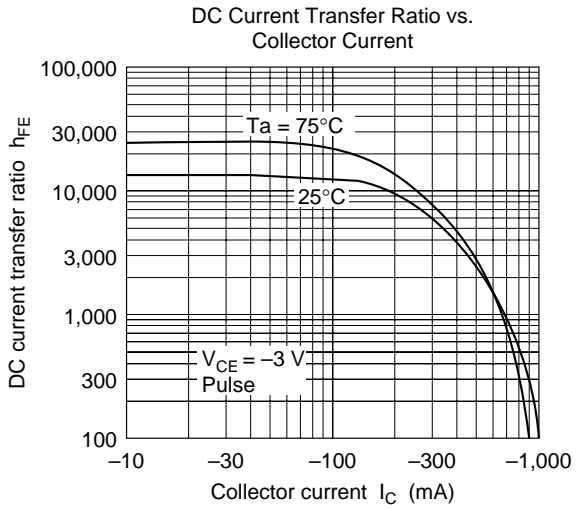
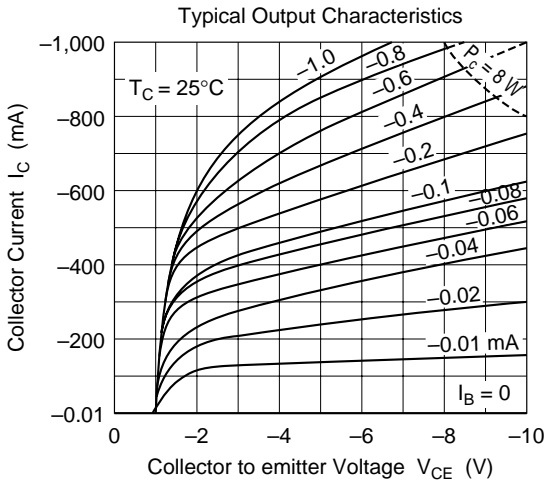
Note: 1. Value at T_c = 25°C

Electrical Characteristics (Ta = 25°C)

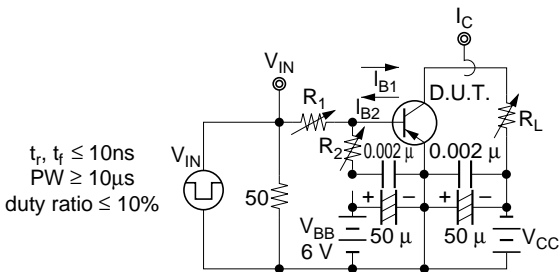
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-60	—	—	V	$I_C = -1 \text{ mA}$, $R_{BE} = \infty$
Collector cutoff current	I_{CBO}	—	—	-1.0	μA	$V_{CB} = -60 \text{ V}$, $I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	-1.0	μA	$V_{EB} = -7 \text{ V}$, $I_C = 0$
DC current transfer ratio	h_{FE}	1000	—	—		$V_{CE} = -3 \text{ V}$, $I_C = -500 \text{ mA}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-2.0	V	$I_C = -500 \text{ mA}$, $I_B = -1 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	-2.0	V	
Turn on time	t_{on}	—	0.7	—	μs	$I_C = -500 \text{ mA}$
Turn off time	t_{off}	—	0.8	—	μs	$I_{B1} = -I_{B2} = -1 \text{ mA}$

Note: 1. Pulse test

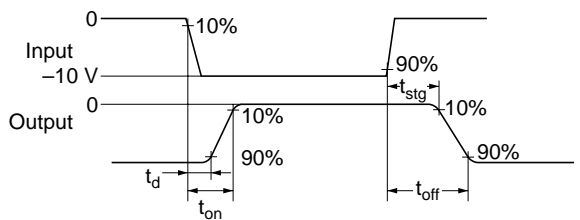




Switching Time Test Circuit

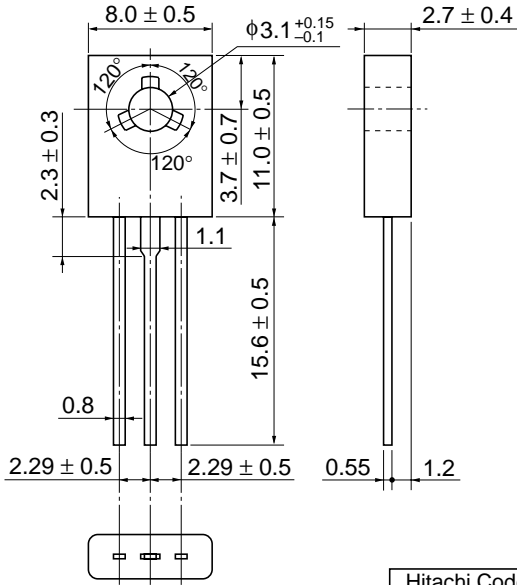


Response Waveform



Package Dimensions

Unit: mm



Hitachi Code	TO-126 Mod
JEDEC	—
EIAJ	—
Mass (reference value)	0.67 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	North America	: http://semiconductor.hitachi.com/
	Europe	: http://www.hitachi-eu.com/hel/ecg
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel: <65>-538-6533/538-8577
Fax : <65>-538-6933/538-3877
URL : <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel: <886>-(2)-2718-3666
Fax : <886>-(2)-2718-8180
Telex : 23222 HAS-TP
URL : <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel : <852>-(2)-735-9218
Fax : <852>-(2)-730-0281
URL : <http://www.hitachi.com.hk>

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